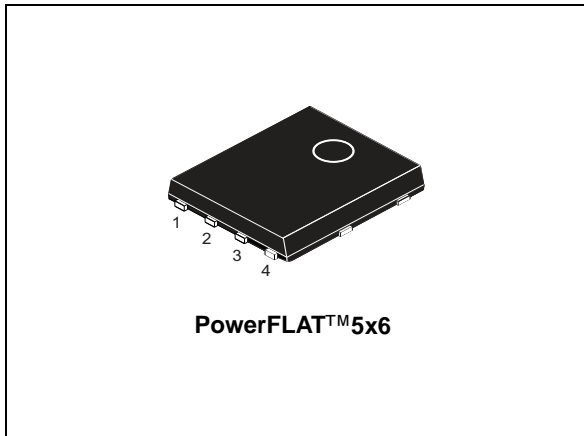


N-channel 30 V, 0.0016  $\Omega$  typ., 160 A STripFET™ H7  
Power MOSFET plus monolithic Schottky in a PowerFLAT™ 5x6

Datasheet - production data



## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STL160NS3LLH7	30 V	0.0021 $\Omega$	160 A

- Very low on-resistance
- Very low Q<sub>g</sub>
- High avalanche ruggedness
- Embedded Schottky diode

## Applications

- Switching applications

## Description

This device exhibits low on-state resistance and capacitance for improved conduction and switching performance.

Figure 1. Internal schematic diagram

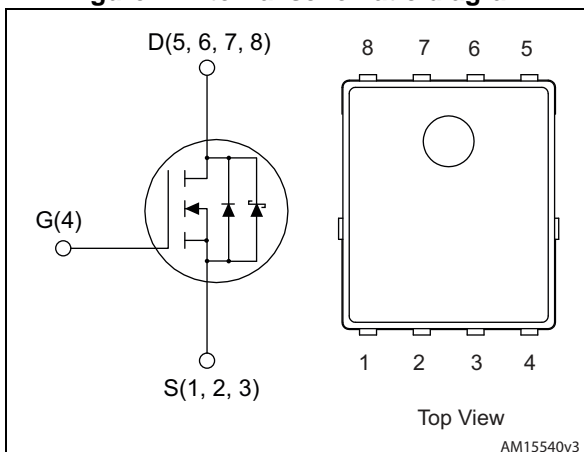


Table 1. Device summary

Order code	Marking	Package	Packaging
STL160NS3LLH7	160NS3LL	PowerFLAT™ 5x6	Tape and reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	160	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	115	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	640	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	36	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	26	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	144	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	84	W
$P_{TOT}^{(3)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	200	mJ
$T_j$	Operating junction temperature	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		$^\circ\text{C}$

1. This value is rated according to  $R_{thj-c}$
2. Pulse width limited by safe operating area
3. This value is rated according to  $R_{thj-pcb}$
4.  $L=1\text{ mH}$ ,  $I_D=20\text{ A}$ ,  $V_{DD}=25\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	31.3	$^\circ\text{C/W}$
$R_{thj-case}$	Thermal resistance junction-case max	1.5	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified).

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	30			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 24\text{ V}$			500	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.2		2.3	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 18\text{ A}$		0.0016	0.0021	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 18\text{ A}$		0.0025	0.0031	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	3245	-	pF
$C_{oss}$	Output capacitance		-	970	-	pF
$C_{riss}$	Reverse transfer capacitance		-	52	-	pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}, I_D = 36\text{ A},$ $V_{GS} = 4.5\text{ V}$ (see <a href="#">Figure 13</a> )	-	20	-	nC
$Q_{gs}$	Gate-source charge		-	9.3	-	nC
$Q_{gd}$	Gate-drain charge		-	5.7	-	nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}, I_D = 18\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 4.5\text{ V}$	-	12.4	-	ns
$t_r$	Rise time		-	21.3	-	ns
$t_{d(off)}$	Turn-off delay time		-	50.7	-	ns
$t_f$	Fall time		-	19.5	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 2 \text{ A}$	-	0.4	0.7	V
$t_{rr}$	Reverse recovery time	$V_{GS} = 0 \text{ V}, I_D = 36 \text{ A},$ $di/dt = 100 \text{ A}/\mu\text{s}$	-	46		ns
$Q_{rr}$	Reverse recovery charge		-	46		nC
$I_{RRM}$	Reverse recovery current		-	2		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

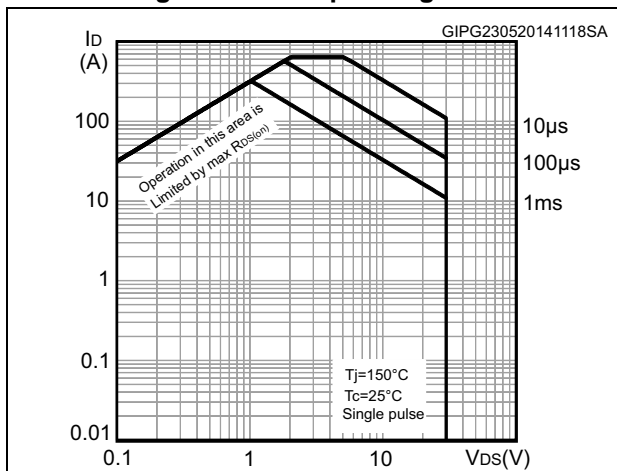


Figure 3. Thermal impedance

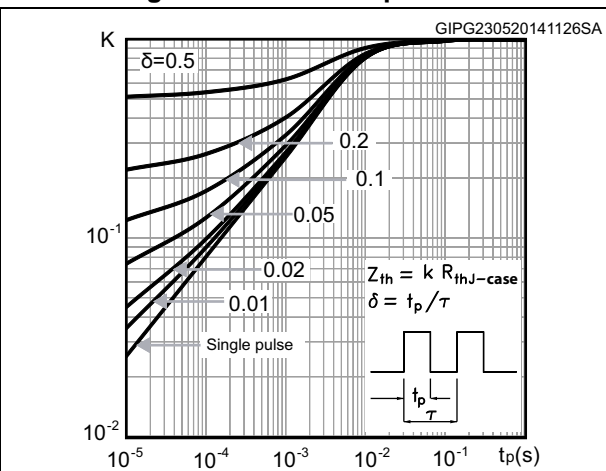


Figure 4. Output characteristics

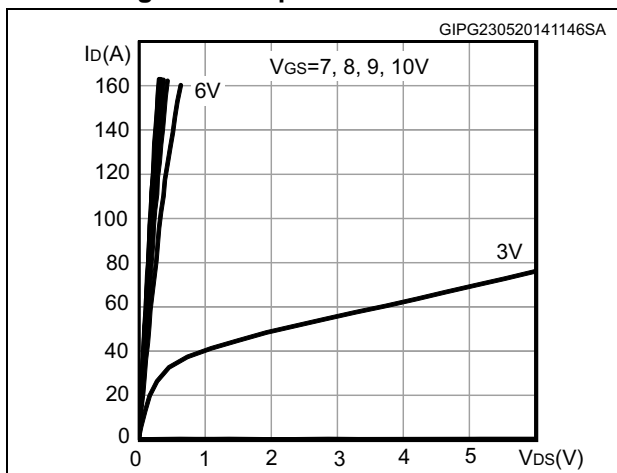


Figure 5. Transfer characteristics

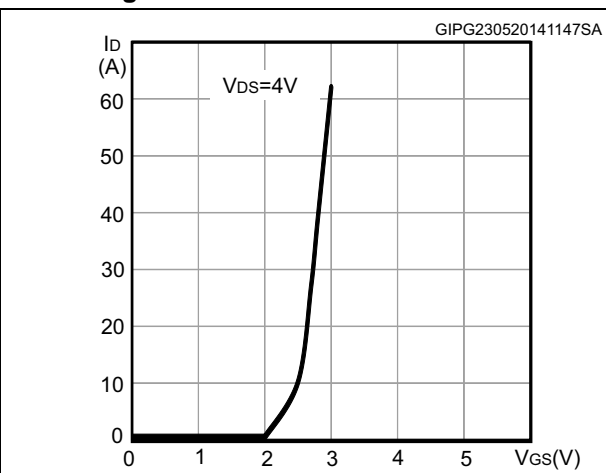


Figure 6. Gate charge vs gate-source voltage

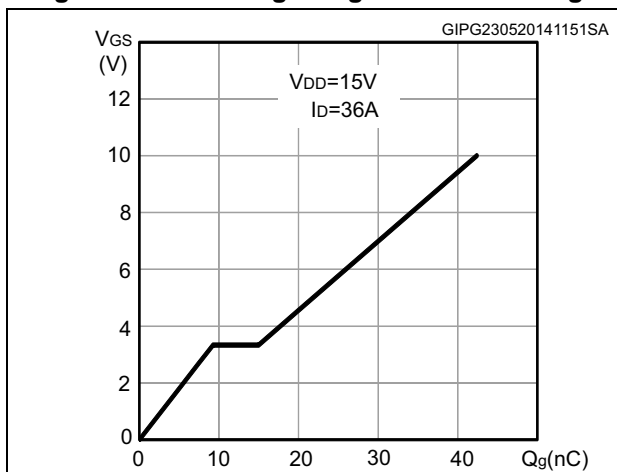


Figure 7. Static drain-source on-resistance

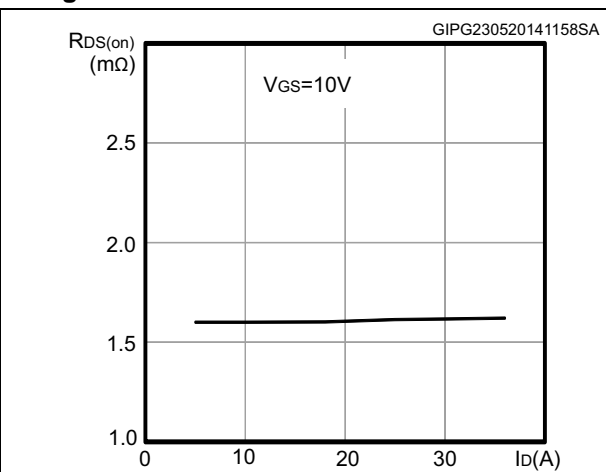


Figure 8. Capacitance variations

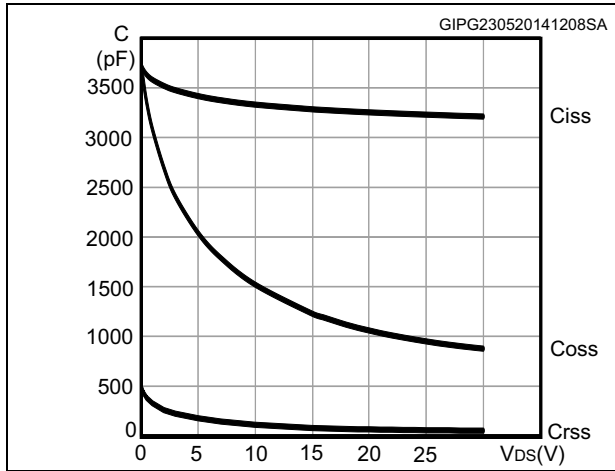


Figure 9. Normalized gate threshold voltage vs temperature

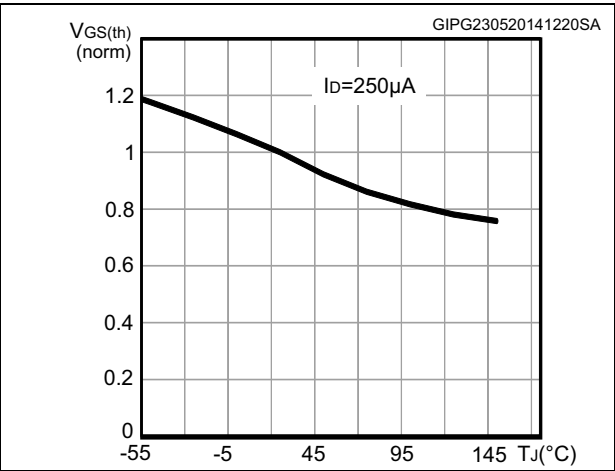


Figure 10. Normalized on-resistance vs temperature

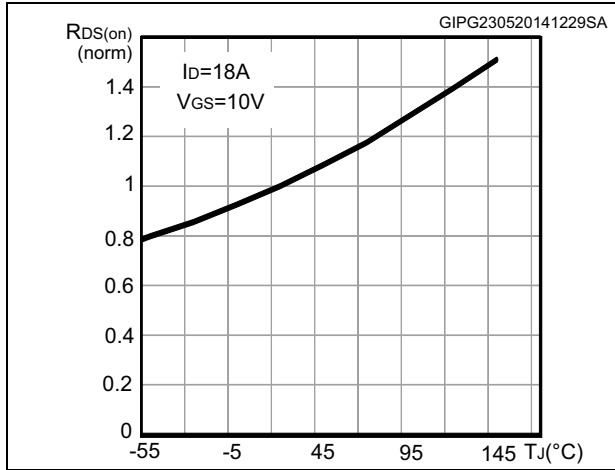
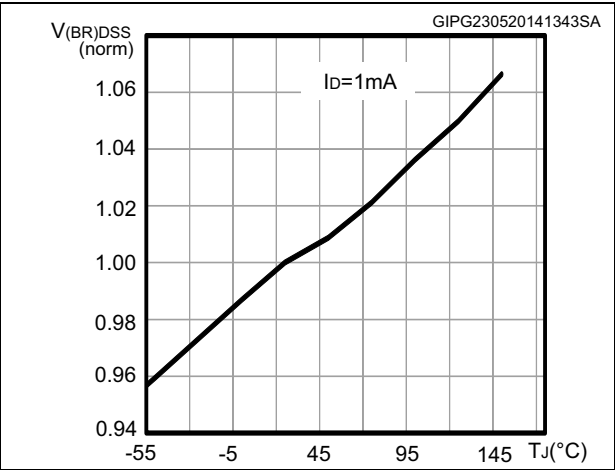


Figure 11. Normalized V<sub>(BR)DSS</sub> vs temperature







## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 18. PowerFLAT™ 5x6 type S-C mechanical data

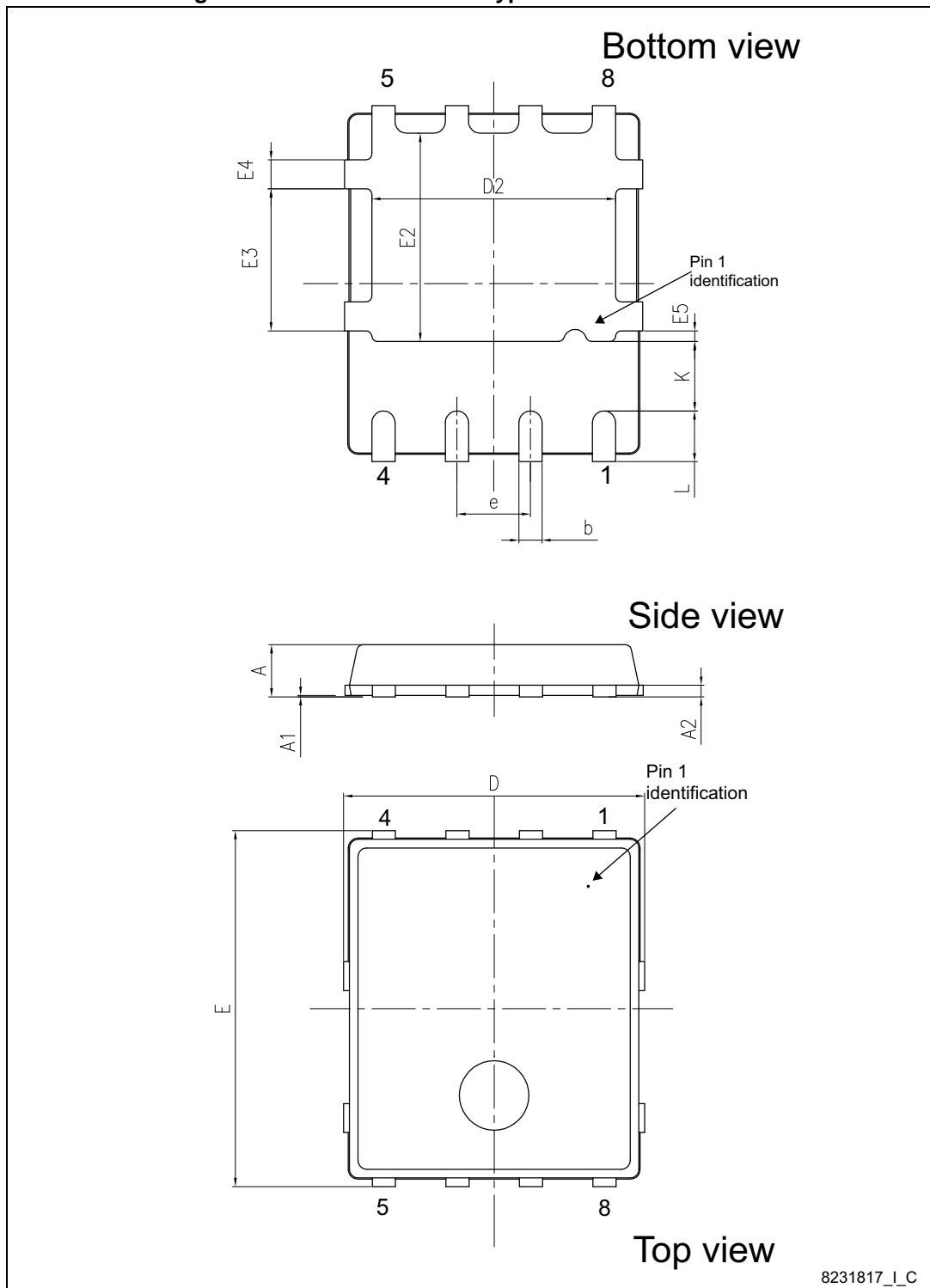
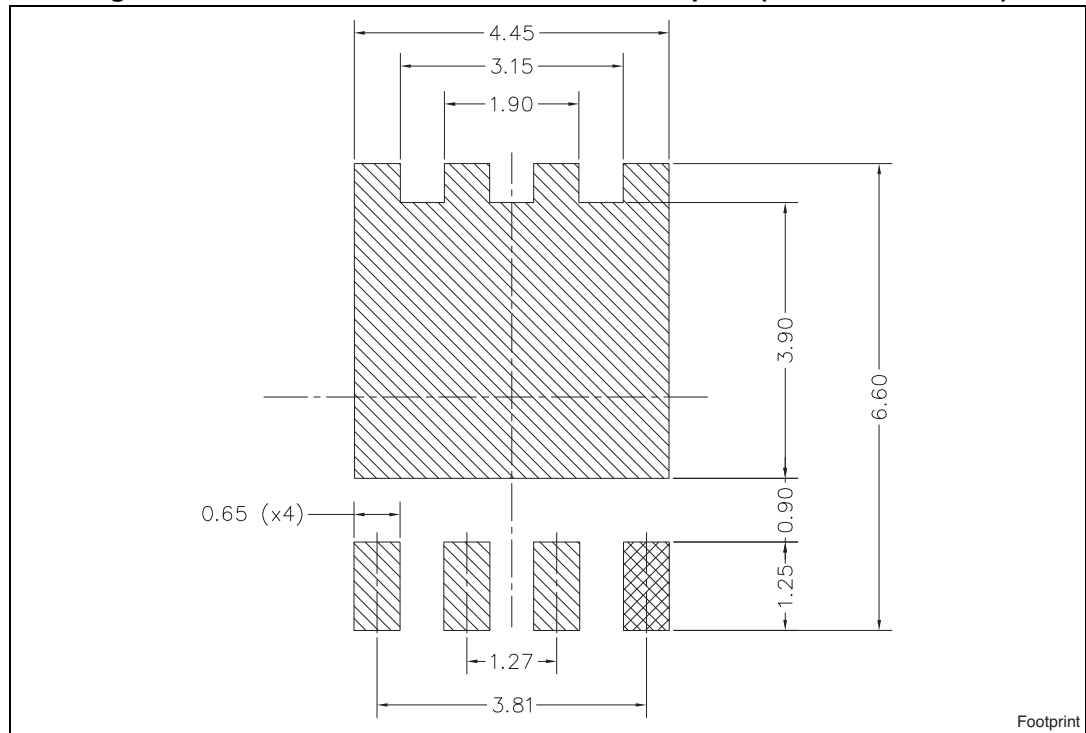


Table 8. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
D2	4.11		4.31
E		6.15	
e		1.27	
e1		0.65	
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
K	1.05		1.35
L	0.715		1.015

Figure 19. PowerFLAT™ 5x6 recommended footprint (dimensions in mm)



# 5 Packaging mechanical data

Figure 20. PowerFLAT™ 5x6 tape<sup>(a)</sup>

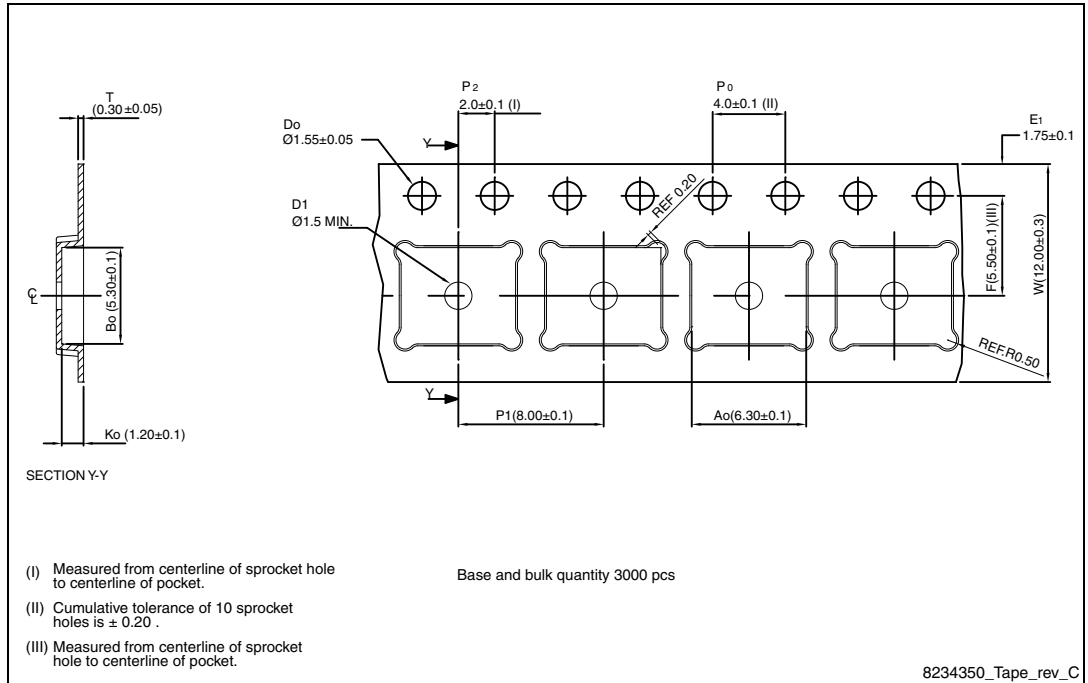
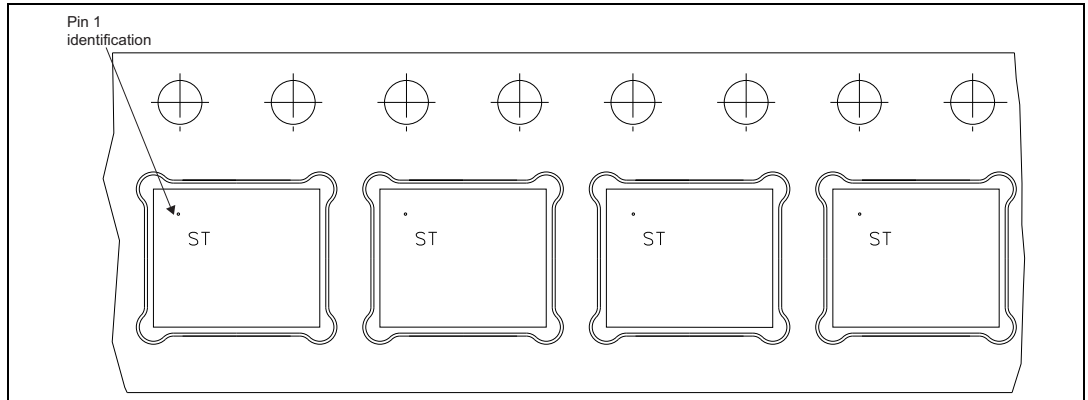


Figure 21. PowerFLAT™ 5x6 package orientation in carrier tape



a. All dimensions are in millimeters.



## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
11-Jun-2013	1	First release.
26-May-2014	2	<ul style="list-style-type: none"><li>– Document status promoted from target to production data</li><li>– Modified: <math>T_J</math> value in <a href="#">Table 2</a></li><li>– Modified: the entire typical values in <a href="#">Table 5, 6, 7</a></li><li>– Added: <a href="#">Section 2.1: Electrical characteristics (curves)</a></li><li>– Updated: <a href="#">Section 4: Package mechanical data</a></li><li>– Minor text changes</li></ul>
18-Jun-2014	3	<ul style="list-style-type: none"><li>– Added: <math>E_{AS}</math> value in <a href="#">Table 2</a></li><li>– Updated: <a href="#">Section 4: Package mechanical data</a></li><li>– Minor text changes</li></ul>
24-Jul-2014	4	<ul style="list-style-type: none"><li>– Modified: title and features</li><li>– Modified: <math>P_{TOT}</math> values in <a href="#">Table 2</a></li><li>– Modified: <math>I_{SD}</math> and <math>I_{SDM}</math> max values in <a href="#">Table 7</a></li><li>– Minor text changes</li></ul>

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